

# Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low  $V_F = 0.53\text{ V}$  at  $I_F = 5\text{ A}$

## NTSB40200CT, NRVTSB40200CT

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable\*
- These Devices are Pb-Free and Halide Free

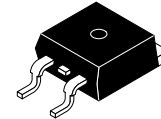
### Typical Applications

- Switching Power Supplies including Telecom AC to DC Power Stages, LED Lighting and ATX
- High Voltage DC-DC Converters
- Freewheeling and OR-ing Diodes
- Output Rectifier in Welding Power Supplies
- Industrial Automation

### Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 s

VERY LOW FORWARD  
VOLTAGE, LOW LEAKAGE  
SCHOTTKY BARRIER  
RECTIFIERS 40 AMPERES,  
200 VOLTS



D<sup>2</sup>PAK-3  
CASE 418B

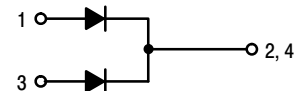
### MARKING DIAGRAM



D<sup>2</sup>PAK-3

A = Assembly Location  
Y = Year  
WW = Work Week  
AKA = Polarity Designator  
G = Pb-Free Package

### PIN CONNECTIONS



### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTSB40200CTG	D <sup>2</sup> PAK-3 (Pb-Free/ Halide Free)	50 / Units / Tube
NTSB40200CTT4G	D <sup>2</sup> PAK-3 (Pb-Free/ Halide Free)	800 / Tape & Reel
NRVTSB40200CTT4G*	D <sup>2</sup> PAK-3 (Pb-Free/ Halide Free)	800 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

# NTSB40200CT, NRVTSB40200CT

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	200	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 125^\circ\text{C}$ ) Per device (Rated $V_R$ , $T_C = 130^\circ\text{C}$ ) Per diode	$I_{F(AV)}$	40 20	A
Peak Repetitive Forward Current (Rated $V_R$ , Square Wave, 20 kHz, $T_C = 115^\circ\text{C}$ ) Per device (Rated $V_R$ , Square Wave, 20 kHz, $T_C = 125^\circ\text{C}$ ) Per diode	$I_{FRM}$	80 40	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	250	A
Operating Junction Temperature	$T_J$	-55 to +150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$
ESD Rating (Human Body Model)		3A	
ESD Rating (Machine Model)		M4	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Typical Thermal Resistance Junction-to-Case Per Diode Junction-to-Case Per Device	$R_{\theta JC}$	1.29 0.79	$^\circ\text{C}/\text{W}$
Junction-to-Ambient Per Device	$R_{\theta JA}$	40	

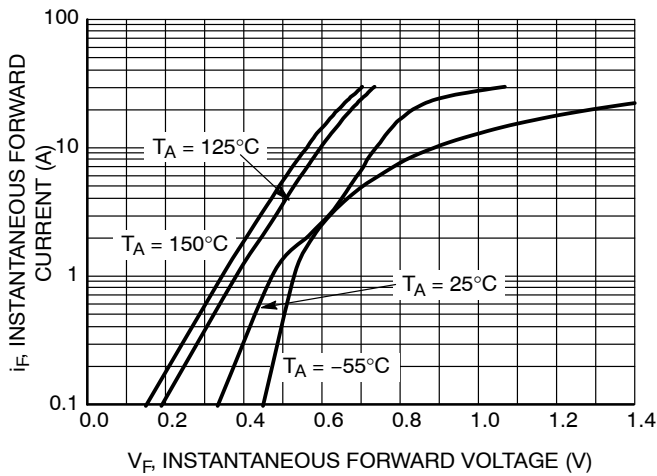
## ELECTRICAL CHARACTERISTICS

Rating	Symbol	Typ	Max	Unit
Instantaneous Forward Voltage (Note 1) ( $I_F = 5\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 10\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 15\text{ A}$ , $T_J = 25^\circ\text{C}$ ) ( $I_F = 20\text{ A}$ , $T_J = 25^\circ\text{C}$ )  ( $I_F = 5\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 10\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 15\text{ A}$ , $T_J = 125^\circ\text{C}$ ) ( $I_F = 20\text{ A}$ , $T_J = 125^\circ\text{C}$ )	$V_F$	0.68 0.74 0.79 0.84  0.53 0.60 0.64 0.68	- - - 1.45  - - - 0.80	V
Instantaneous Reverse Current (Note 1) ( $V_R = 180\text{ V}$ , $T_J = 25^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 25^\circ\text{C}$ )  ( $V_R = 180\text{ V}$ , $T_J = 125^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ )	$I_R$	3 5  5.3 7	- 100  - 30	$\mu\text{A}$ $\mu\text{A}$  mA mA

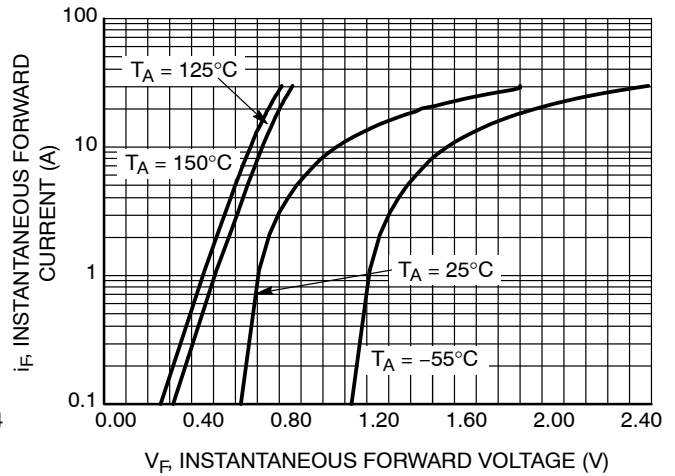
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

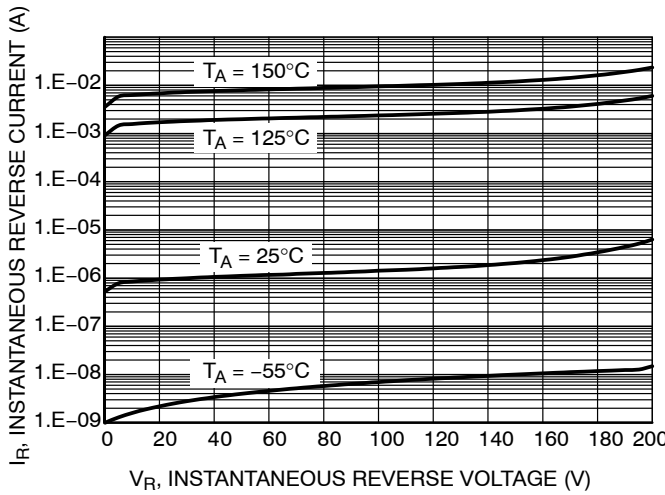
TYPICAL CHARACTERISTICS



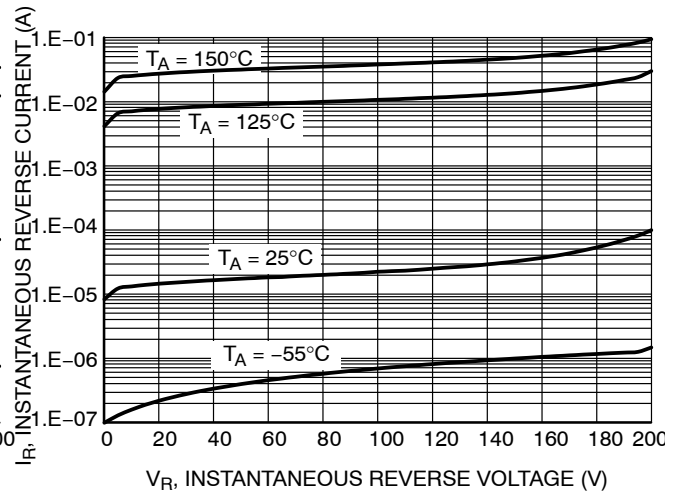
**Figure 1. Typical Instantaneous Forward Characteristics**



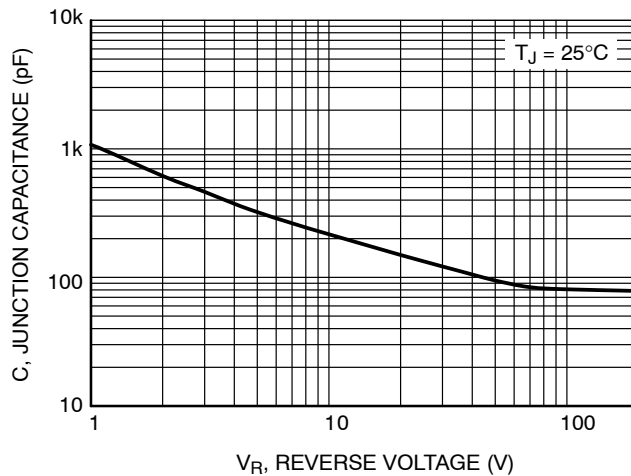
**Figure 2. Maximum Instantaneous Forward Characteristics**



**Figure 3. Typical Reverse Characteristics**



**Figure 4. Maximum Reverse Characteristics**



**Figure 5. Typical Junction Capacitance**

# NTSB40200CT, NRVTSB40200CT

## TYPICAL CHARACTERISTICS

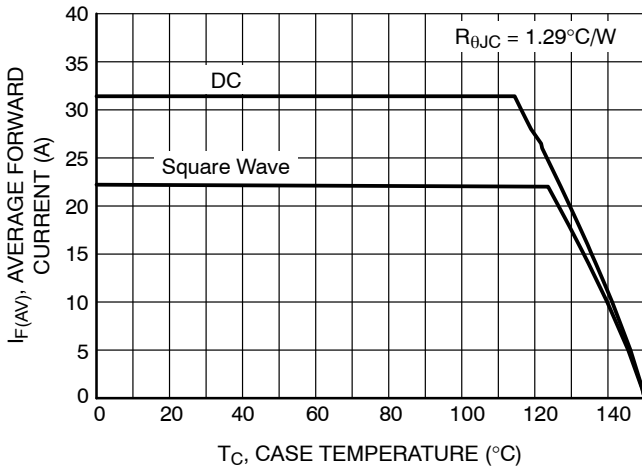


Figure 6. Current Derating per Diode

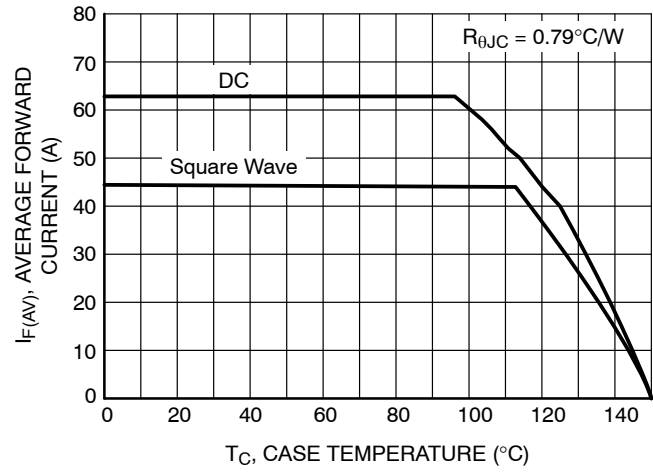


Figure 7. Current Derating per Device

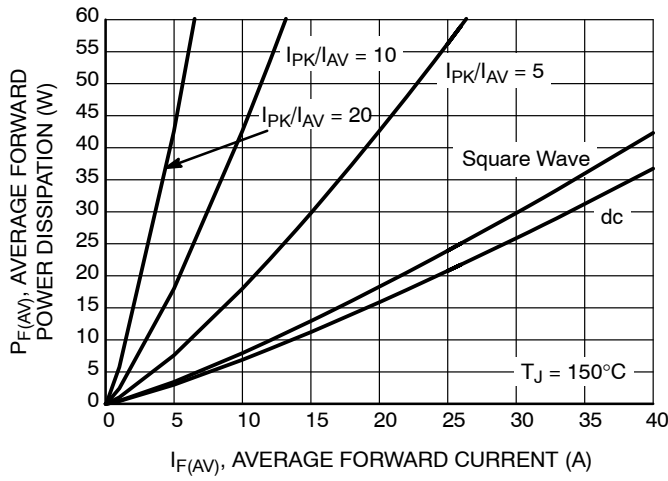


Figure 8. Forward Power Dissipation

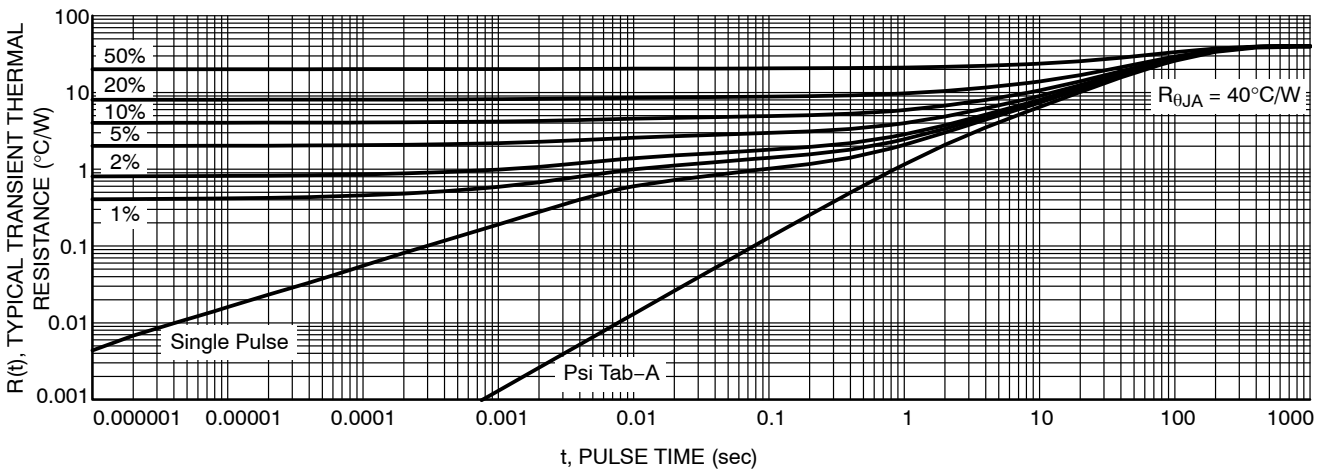


Figure 9. Typical Transient Thermal Response per Device (NTSB40200CTG)

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

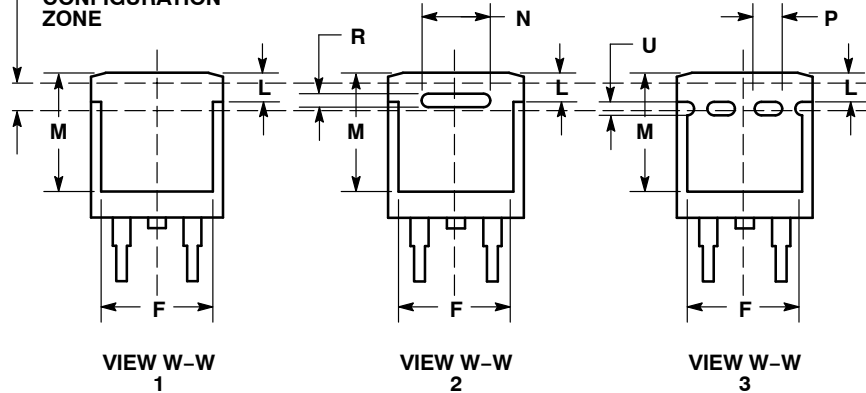
SCALE 1:1



- NOTES:
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  - CONTROLLING DIMENSION: INCH.
  - 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

VARIABLE CONFIGURATION ZONE



- |                                                                       |                                                              |                                                                  |                                                                       |                                                                  |                                                                       |
|-----------------------------------------------------------------------|--------------------------------------------------------------|------------------------------------------------------------------|-----------------------------------------------------------------------|------------------------------------------------------------------|-----------------------------------------------------------------------|
| STYLE 1:<br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | STYLE 2:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE<br>4. DRAIN | STYLE 3:<br>PIN 1. ANODE<br>2. CATHODE<br>3. ANODE<br>4. CATHODE | STYLE 4:<br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | STYLE 5:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE<br>4. ANODE | STYLE 6:<br>PIN 1. NO CONNECT<br>2. CATHODE<br>3. ANODE<br>4. CATHODE |
|-----------------------------------------------------------------------|--------------------------------------------------------------|------------------------------------------------------------------|-----------------------------------------------------------------------|------------------------------------------------------------------|-----------------------------------------------------------------------|

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**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

**GENERIC  
MARKING DIAGRAM\***



- xx = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package
- AKA = Polarity Indicator

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

**SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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